

ITA6V1U1

Application Specific Discretes A.S.D.TM

TRANSIL™ ARRAY FOR DATALINE PROTECTION

APPLICATIONS

Data transmission lines protection:

- Unipolar signal up to 5.5V
- Bipolar signal in the +/- 2.5V range

FEATURES

- HIGH SURGE CAPABILITY TRANSIL ARRAY IPP = 40 A (8/20µs)
- PEAK PULSE POWER: 300 W (8/20µs)
- UP TO 6 UNIDIRECTIONAL TRANSIL FUNC-TIONS
- LOW CLAMPING FACTOR (V_{CL} / V_{BR}) AT HIGH CURRENT LEVEL
- LOW LEAKAGE CURRENT
- ESD PROTECTION UP TO 15kV

DESCRIPTION

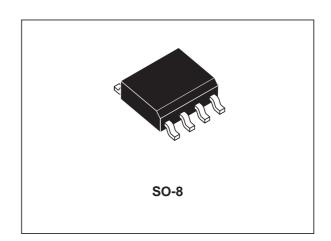
Transil diode arrays provide high overvoltage protection by clamping action. Their instantaneous response to transient overvoltages makes them particularly suited to protect voltage sensitive devices such as MOS Technology and low voltage supplied IC's.

The ITA series allies high surge capability against energetic pulses with high voltage performance against ESD.

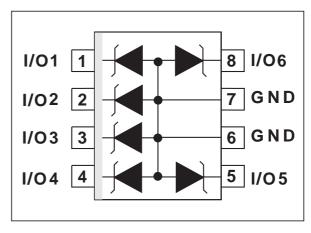
COMPLIES WITH THE FOLLOWING STANDARDS:

IEC 1000-4-2 : level 4 IEC 1000-4-4 : level 4 IEC 1000-4-5 : level 2

MIL STD 883C - Method 3015-6 : class 3 (human body model)



FUNCTIONAL DIAGRAM

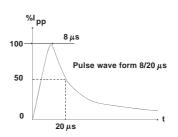


August 2001- Ed: 2

ABSOLUTE MAXIMUM RATINGS (T_{amb} = 25°C)

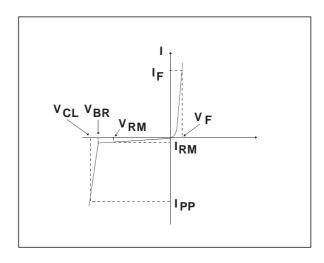
Symbol	Parameter	Value	Unit
P _{PP}	Peak pulse power dissipation (8/20μs) (see note 1)	300	W
I _{PP}	Peak pulse current (8/20μs) (see note 1)	40	Α
l ² t	Wire I ² t value (see note 1)	0.6	A ² s
T _{stg} T _j	Storage temperature range Maximum operating junction temperature	- 55 to + 150 125	ိုပ္
TL	Maximum lead temperature for soldering du	260	°C

Note 1 : For surges greater than the specified maximum value, the I/O will first present a short-circuit and after an open circuit caused by the wire melting.



ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C)

Symbol	Parameter				
V_{RM}	Stand-off voltage				
V_{BR}	Breakdown voltage				
V _{CL}	Clamping voltage				
I _{RM} Leakage current @ V _{RM}					
I _{PP} Peak pulse current					
αΤ	Voltage temperature coefficient				
С	Junction capacitance				
V _F Forward voltage drop					



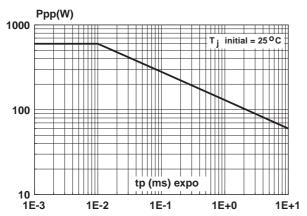
Types	I _{RM} @	V _{RM}	V _{BR}	@ I R	V _{CL}	@ l PP	V _{CL}	@ I PP	αΤ	С	V _F @) I F
	max.		min.		max.	8/20μ s	max.	8/20μ s	max.	max.	max.	
			note 2		note 2		note 2			note 3		
	μ Α	٧	V	mA	V	Α	V	Α	10 ⁻⁴ /°C	рF	V	Α
ITA6V1U1	10	5	6.1	1	10	10	12	25	4	1500	1.3	1

Note 2 : Between I/O pin and ground. Note 3 : Between I/O pin and ground, at 0V Bias. F = 1MHz.

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1E+02

Fig. 1: Typical peak pulse power versus exponential pulse duration.



oit of Fig.

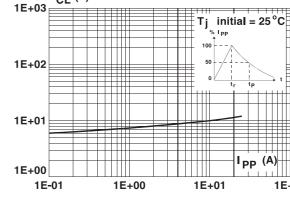


Fig. 2: Clamping voltage versus peak pulse

current (exponential waveform 8/20 μs).

V_{CL} (V)

Fig. 3: Peak current I_{DC} inducing open circuit of the wire for one input/output versus pulse duration (typical values).

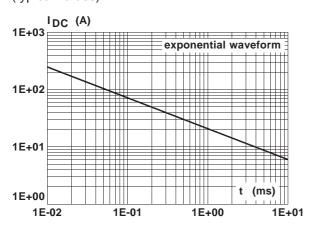


Fig. 4 : Junction capacitance versus reverse applied voltage for one input/output (typical values).

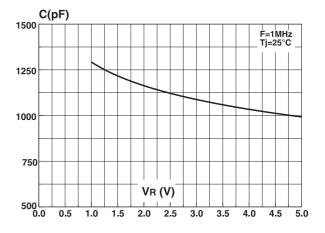
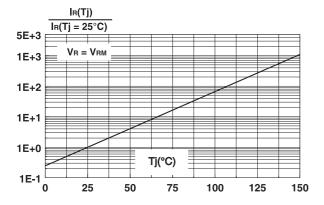


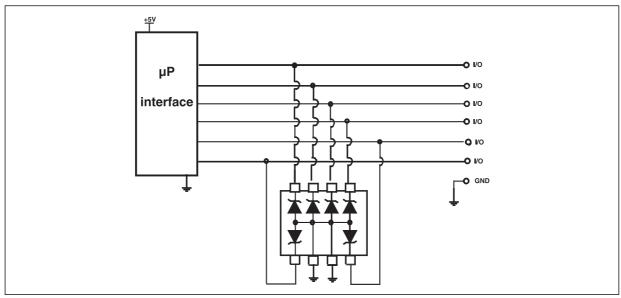
Fig. 5: Relative variation of leakage current versus junction temperature



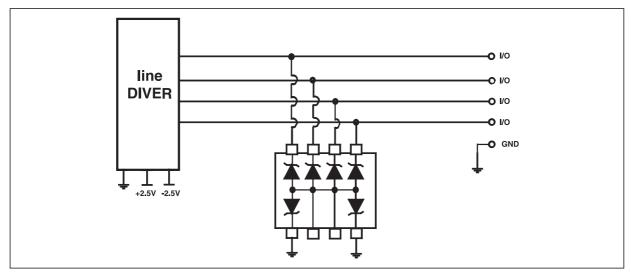
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APPLICATION INFORMATION

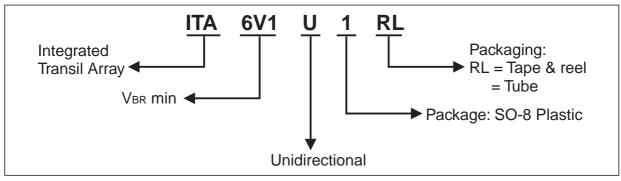
Typical application 1 : μ P I/O lines



Typical application 2: +/-2.5V Data lines



ORDER CODE



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MARKING

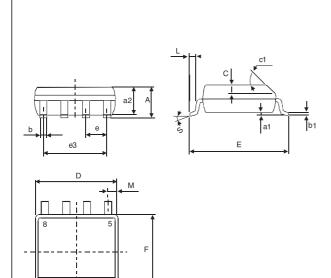
TYPE	MARKING		
ITA6V1U1	6V1U1		

Packaging: Preferred packaging is tape and reel.

Weight: 0.08g.

PACKAGE MECHANICAL DATA

SO-8 (Plastic)



	DIMENSIONS									
REF.	Mi	llimetr	es	Inches						
	Min.	Тур.	Max.	Min.	Тур.	Max.				
Α			1.75			0.069				
a1	0.1		0.25	0.004		0.010				
a2			1.65			0.065				
b	0.35		0.48	0.014		0.019				
b1	0.19		0.25	0.007		0.010				
С		0.50			0.020					
c1			45°	(typ)						
D	4.8		5.0	0.189		0.197				
Е	5.8		6.2	0.228		0.244				
е		1.27			0.050					
e3		3.81			0.150					
F	3.8		4.0	0.15		0.157				
L	0.4		1.27	0.016		0.050				
M			0.6			0.024				
S	8° (max)									

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